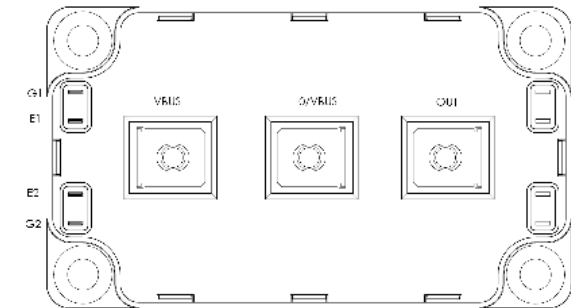
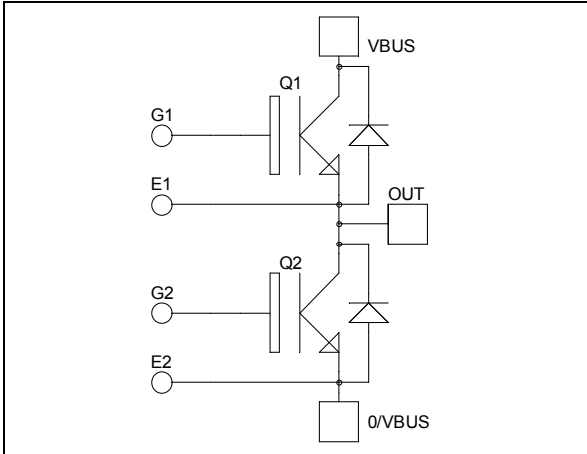


Phase leg
High speed Trench + Field Stop
IGBT4 Power module

$V_{CES} = 1200V$
 $I_C = 300A @ T_c = 80^\circ C$



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- **High speed Trench + Field Stop IGBT 4**
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- M5 power connectors

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V_{CES}	Collector - Emitter Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	500
		$T_C = 80^\circ C$	300
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	960
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	1500	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			200	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$	1.78	$T_j = 25^\circ C$ 2.05	2.42	V
		$T_j = 150^\circ C$		2.6		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 10.4 mA$	5.3	5.8	6.3	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			480	nA

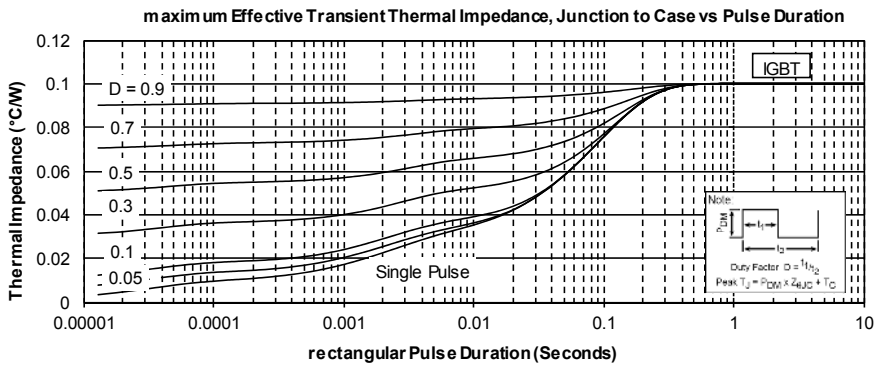
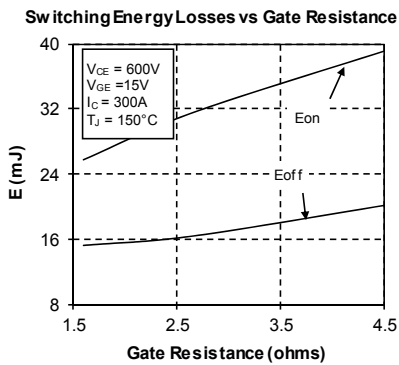
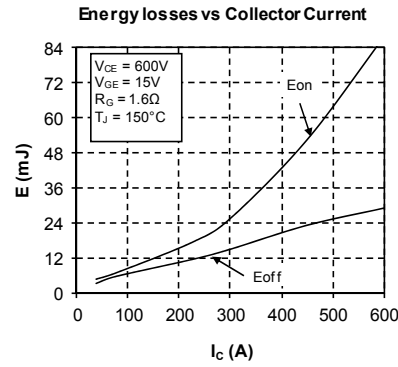
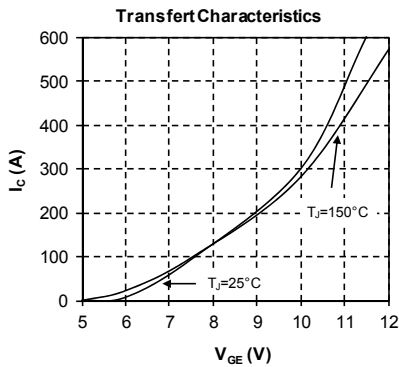
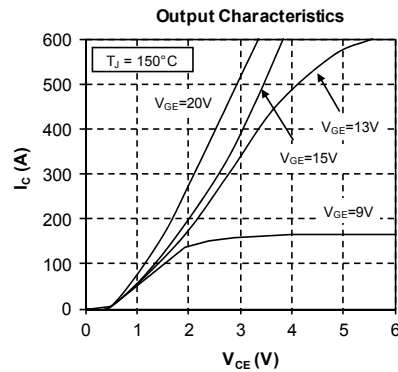
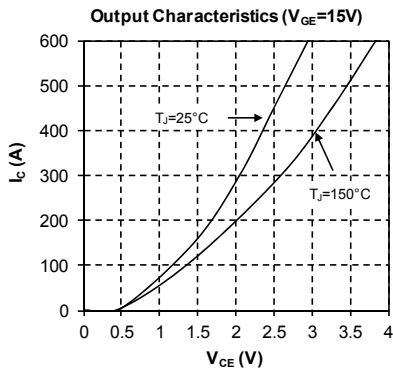
Dynamic Characteristics (Per IGBT)

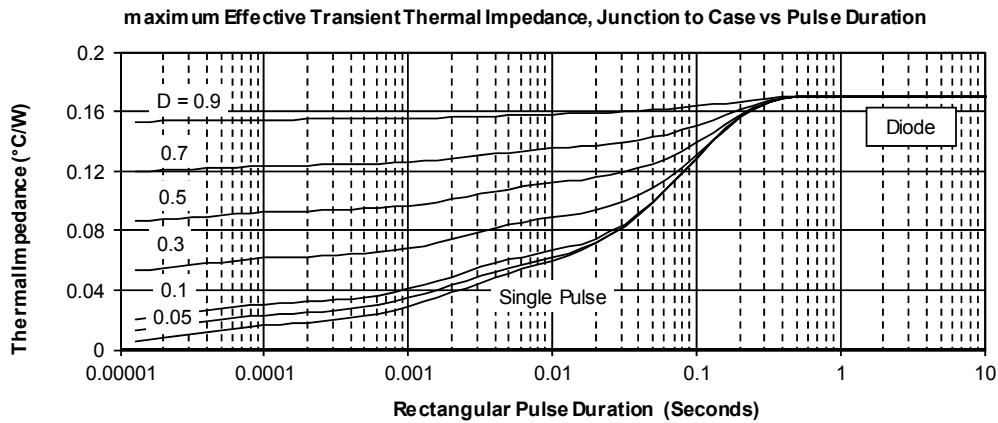
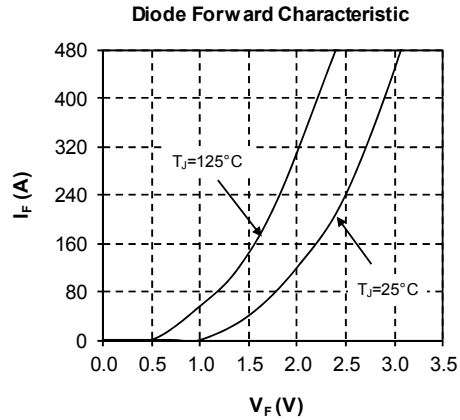
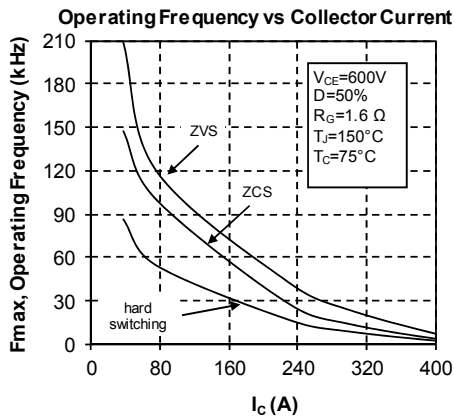
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		17.6		nF
C_{oes}	Output Capacitance			1		
C_{res}	Reverse Transfer Capacitance			0.9		
Q_G	Gate charge	$V_{GE} = 15V, I_C = 300A$ $V_{CE} = 960V$		1290		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 300A$ $R_G = 1.6\Omega$		30		ns
T_r	Rise Time			57		
$T_{d(off)}$	Turn-off Delay Time			290		
T_f	Fall Time			16		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 300A$ $R_G = 1.6\Omega$		30		ns
T_r	Rise Time			49		
$T_{d(off)}$	Turn-off Delay Time			366		
T_f	Fall Time			48		
E_{on}	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 300A$	$T_j = 150^\circ C$	26		mJ
E_{off}	Turn off Energy	$R_G = 1.6\Omega$		16		
R_G	Integrated gate resistor			2.5		Ω
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 600V$ $t_p \leq 10\mu s; T_j = 150^\circ C$		1000		A
R_{thJC}	Junction to Case Thermal Resistance				0.1	$^\circ C/W$

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage				1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$			400	μA
I_F	DC Forward Current	$T_c = 60^\circ C$		240		A
V_F	Diode Forward Voltage	$I_F = 240A$		2.5	3.5	V
		$I_F = 480A$		3		
		$I_F = 240A$	$T_j = 125^\circ C$	1.8		
t_{rr}	Reverse Recovery Time	$I_F = 240A$ $V_R = 800V$ $di/dt = 800A/\mu s$	$T_j = 25^\circ C$	265		ns
			$T_j = 125^\circ C$	350		
Q_{rr}	Reverse Recovery Charge	$I_F = 240A$ $V_R = 800V$ $di/dt = 800A/\mu s$	$T_j = 25^\circ C$	2.24		μC
			$T_j = 125^\circ C$	11.6		
R_{thJC}	Junction to Case Thermal Resistance				0.17	$^\circ C/W$

Typical Performance Curve





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